* Circuit Description

* transistor model statement
.model BCxxx NPN (Is=1.8104e−15 Bf=100 Vaf=35V)

VCE 3 0 0V
R1 3 2 .0001
IB 0 1 10u

* device under test

Q1 2 1 0 0 BCxxx

* Print analysis results
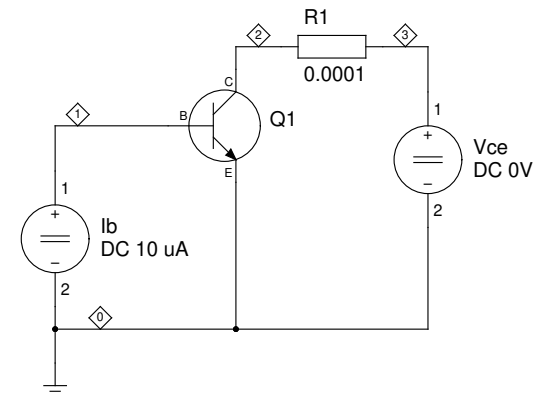.PRINT DC V(2) I(R1)

* vary Vce from 0V to 10V in steps of 10mV
.DC VCE 0V 10V 10mV

* vary Vce from 0V to 10V in steps of 10mV,
* vary Ib from 1 uA to 10 uA in stpes of 1 uA
*.DC VCE 0V 10V 100mV IB 1u 10u 1u

.end

R1

0.0001

Q1

Ib
DC 10 uA

Vce
DC 0V